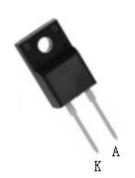
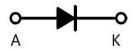


FRED Ultrafast Soft Recovery Diode, 20A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
VR	400 V	
lf(AV)	20A	
trr	22ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	VRRM	Test conditions	400	V
Continuous forward current	lf(AV)	Tc =110°C	20	
Single pulse forward current	lfsm	Tc =25°C	200	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	40	
Operating junction	Tj		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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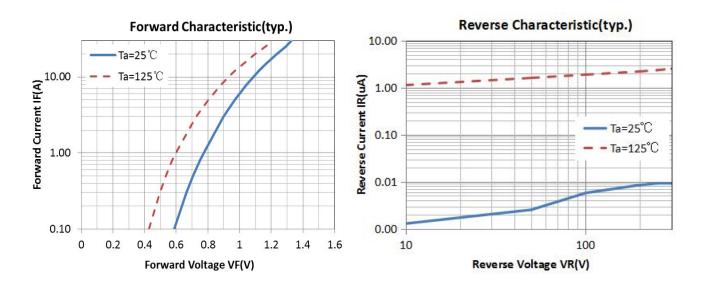


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units	
Breakdown voltage Blocking voltage	VBR, V _R	Ir=100µA	400				
Forward voltage	VF	IF=20 A		1.25	1.5	V	
(Per Diode)		IF=20 A, Tj =125°C		1.1	1.4		
Reverse leakage	lr	Vr= Vrrm			20		
current(Per Diode)		Tj=150°C, Vr=400V			200	μΑ	
Reverse recovery	trr	I _F =0.5A, I _R =1A, I _{RR} =0.25A		30	50		
time(Per Diode)		I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		22	30	ns	

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	3.0	°C/W

Electrical performance (typic)

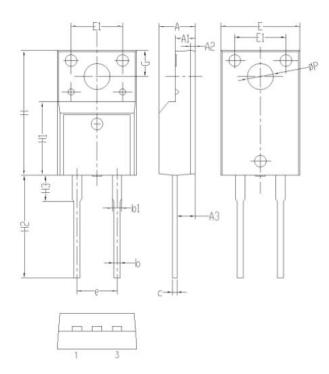


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Package Information

TO-220F-2 PACKAGE



Symbol	Dimensions(millimeter		
Symbol	Min.	Max.	
Α	4.35	4.75	
A1	2.30	2.70	
A2	0.40	0.80	
A3	2.10	2.50	
b	0.60	1.00	
b1	1.00	1.40	
С	0.30	0.70	
е	4.60	5.40	
E	9.80	10.2	
E1	6.30	6.70	
Н	15.6	16.0	
H1	8.80	9.20	
H2	12.9	13.5	
H3	3.10	3.50	
G	3.10	3.50	
ΦР	3.10	3.50	

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